

Silicon NPN Power Transistors

2SC2608

DESCRIPTION

- With TO-3 package
- Complement to type 2SA1117
- High power dissipation

APPLICATIONS

- For power amplifier applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

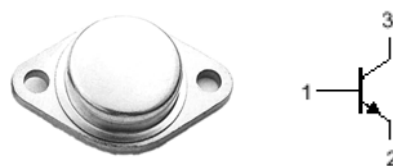


Fig.1 simplified outline (TO-3) and symbol

ABSOLUTE MAXIMUM RATINGS($T_c=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	200	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	6	V
I_C	Collector current		17	A
P_C	Collector power dissipation	$T_c=25^{\circ}\text{C}$	200	W
T_j	Junction temperature		150	$^{\circ}\text{C}$
T_{stg}	Storage temperature		-55~150	$^{\circ}\text{C}$

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CHARACTERISTICS

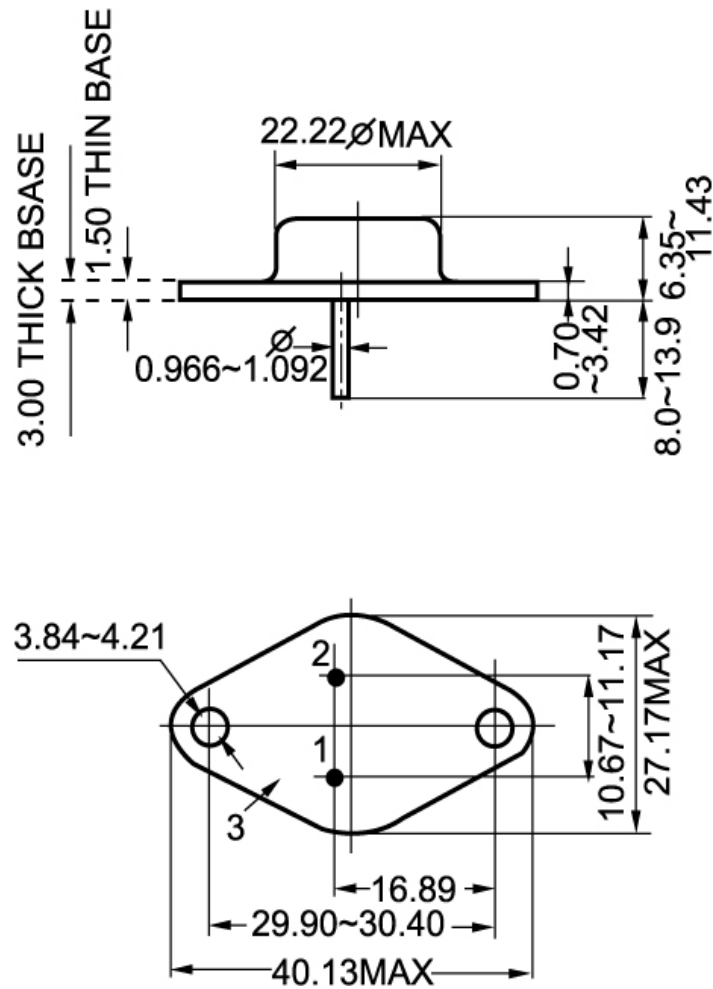
T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-emitter breakdown voltage	I _C =25mA ; I _B =0	200			V
V _{(BR)CBO}	Collector-base breakdown voltage	I _C =1mA ; I _E =0	200			V
V _{(BR)EBO}	Emitter-base breakdown voltage	I _E =1mA ; I _C =0	6			V
V _{CE(sat)}	Collector-emitter saturation voltage	I _C =8A; I _B =0.8A			2.0	V
I _{CBO}	Collector cut-off current	V _{CB} =200V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =6V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =8A ; V _{CE} =4V	20			
f _T	Transition frequency	I _C =1A ; V _{CE} =12V		20		MHz

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PACKAGE OUTLINE

Fig.2 outline dimensions (unindicated tolerance: $\pm 0.1\text{mm}$)